

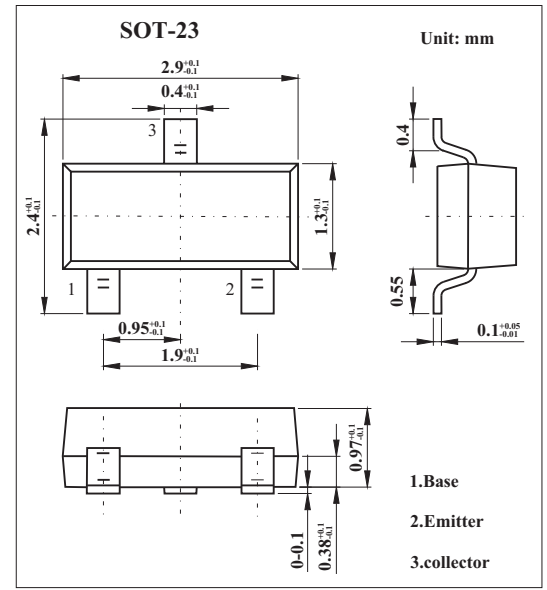
SOT-23 Plastic-Encapsulate Transistors

Features

- Collector Power Dissipation: PC=0.3W
- Collector Current: IC=-1.5A
- PNP General Purpose Transistors

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-40	V
Collector-Emitter Voltage	V _{CEO}	-25	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current -Continuous	I _C	-1.5	A
Collector Power Dissipation	P _C	0.3	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to 150	°C

PACKAGE INFORMATION

Device	Package	Shipping
S9014	SOT-23	3000/Tape&

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100 μA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100 μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-40V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-1V, I _C =-100mA	200		350	
		V _{CE} =-1V, I _C =-800mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-800mA, I _B =-80mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-800mA, I _B =-80mA			-1.2	V
Transition frequency	f _T	V _{CE} = -10V, I _C = -50mA, f=30MHz	100			MHz
output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			20	pF

■ Marking

Marking	Y2
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RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

